



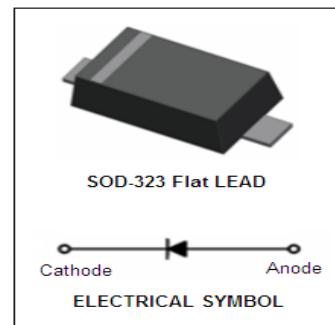
SLS SEMICONDUCTOR (SHENZHEN) CO.,LTD.

SOD-323 封装二极管/SOD-323 Plastic-Encapsulate Diodes**SD103AWS/SD103BWS/SD103CWS (SCHOTTKY DIODES)****特点/Features :**

- 正向导通电压低；
- 环保保护结构提供瞬态保护；
- 极小的恢复时间；
- 极小的反向电容；

用途/Applications :

- 高速开关电路。

**极限参数/Absolute maximum ratings(Ta=25°C)**

Parameter	Symbol	SD103AWS	SD103BWS	SD103CWS	Unit
Peak Repetitive Peak Reverse Voltage	V_{RRM}				
Working Peak	V_{RWM}	40	30	20	V
DC Blocking Voltage	V_R				
RMS Reverse Voltage	$V_{R(RMS)}$	28	21	14	V
Forward Continuous Current	I_{FM}		350		mA
Repetitive Peak Forward Current (@t≤1S)	I_{FSM}		1.5		A
Power Dissipation	P_d		200		mW
Thermal Resistance Junction To Ambient	$R_{\theta JA}$		300		°C/mW
Storage Temperature	Tstg		-65~125		°C

电性能参数/Electrical characteristics (Ta=25°C)

参数/Parameter	符号	测试条件	最小值	典型值	最大值	单位
Reverse Breakdown Voltage SD103AWS SD103BWS SD103CWS	$V_{(BR)R}$	$I_R=100 \mu A$ $I_R=100 \mu A$ $I_R=100 \mu A$	40 30 20			V
Forward Voltage	V_F	$I_F=20mA$ $I_F=200mA$			0.37 0.60	V
Reverse Current SD103AWS SD103BWS SD103CWS	I_{RM}	$V_R=30V$ $V_R=30V$ $V_R=30V$			5.0	μA
Capacitance Between Terminals	C_T	$V_R=0V, f=1.0MHz$			50	pF
Reverse Recovery Time	t_{rr}	$I_F=I_R=200mA,$ $I_{rr}=0.1 \times I_R, R_L=100 \Omega$		10		nS

印章/ Marking:

型号	SD103AWS	SD103BWS	SD103CWS
印章	S4	S5	S6



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典型特性曲线图/Typical Characteristics

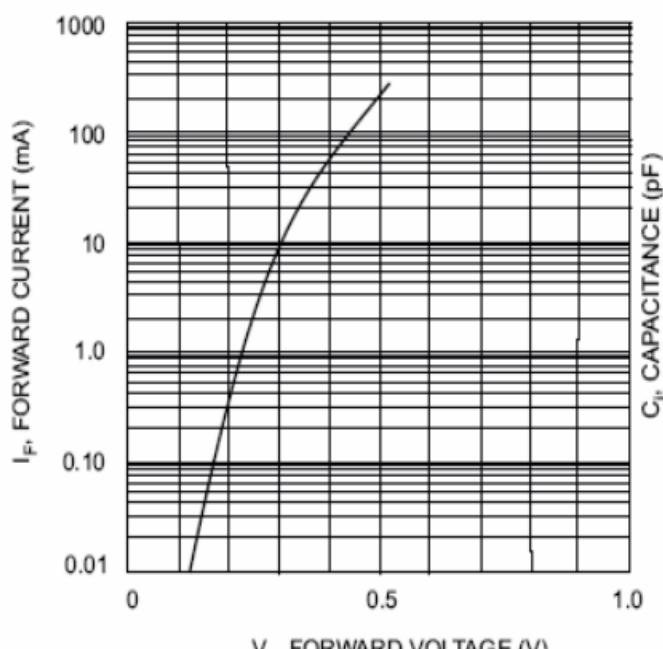


Fig. 1 Typical Forward Characteristics

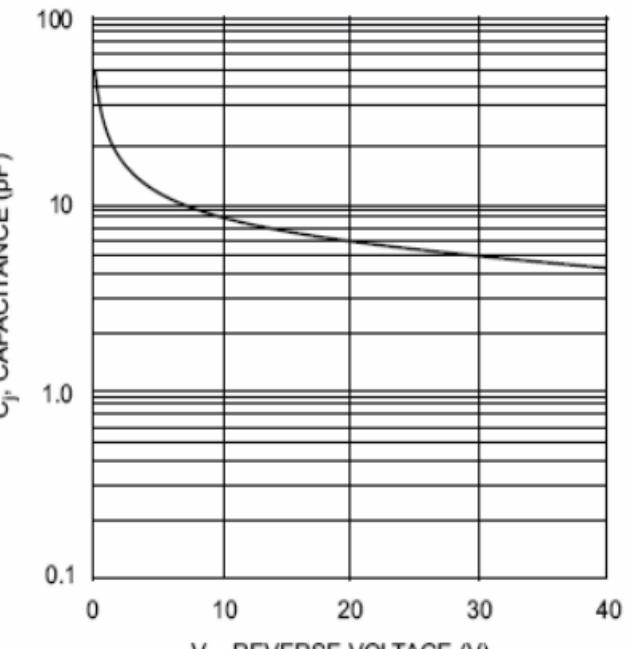


Fig. 2 Typ. Junction Capacitance vs Reverse Voltage